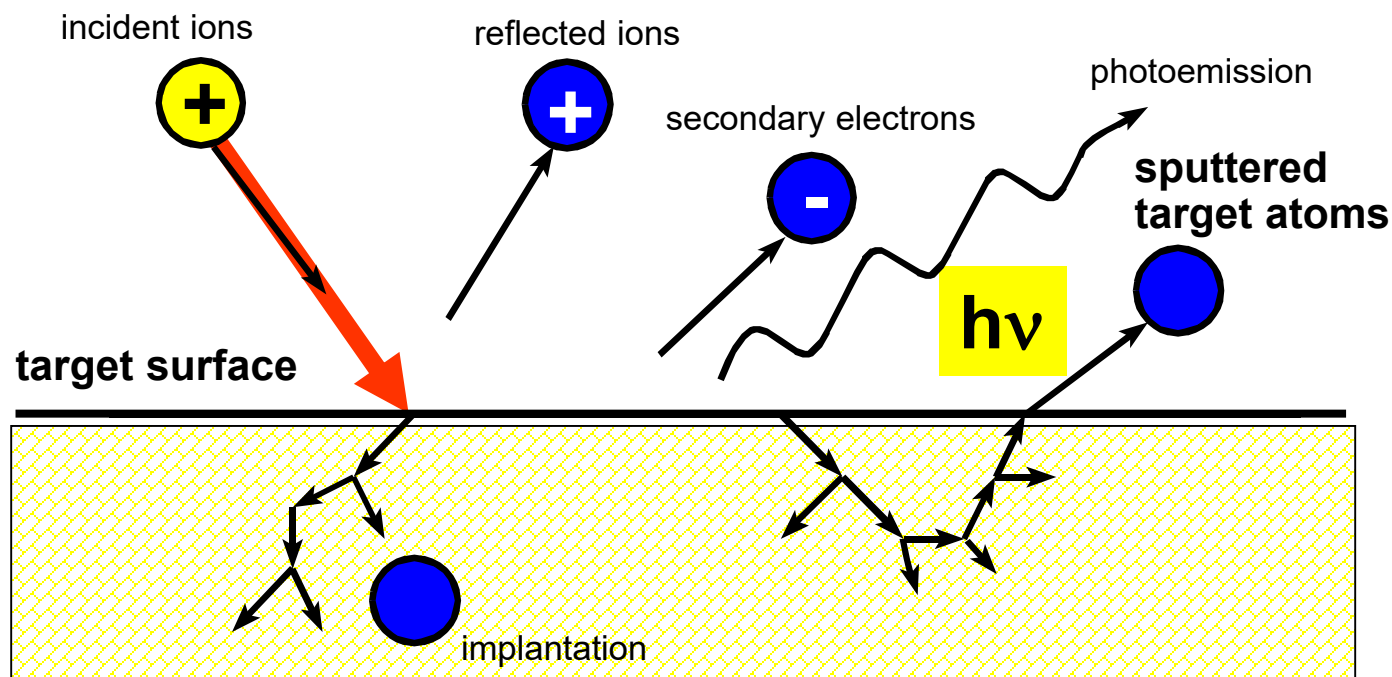


Q11 What are the basic steps/mechanism of sputtering? (elementary processes)

- 1) Collision cascade in the target by target atom release (later on: transport of the atom towards the substrate / condensation → film formation
- 2) Reflection of argon ions
- 3) Argon ion implantation
- 4) ...
- 5) ...
- 6) ...

Elementary processes of sputtering



Interaction of ions with the surface

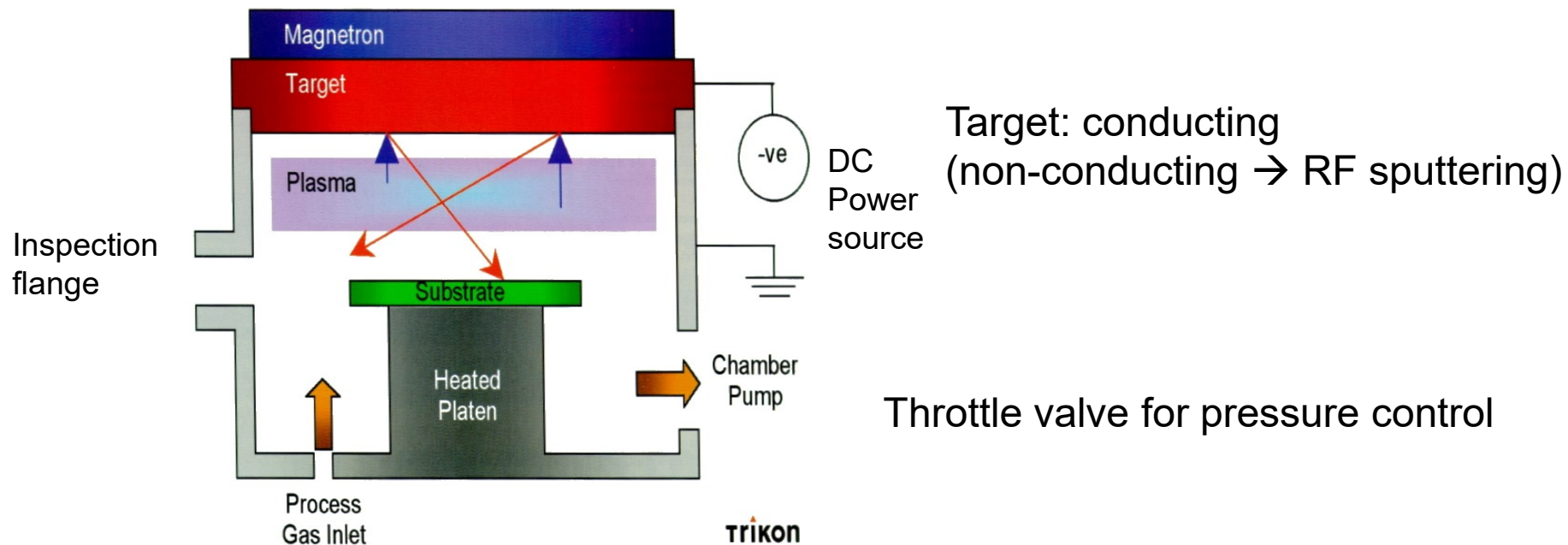
reflection secondary electrons change of stoichiometry
lattice defects radiation damages ion implantation

Sputtering:

Generation of a collision cascade

It differs, if the last collision hits an atom in the bulk or at the surface of the target.
Only in the latter case an emission takes place - efficiency 5% to 25 %!

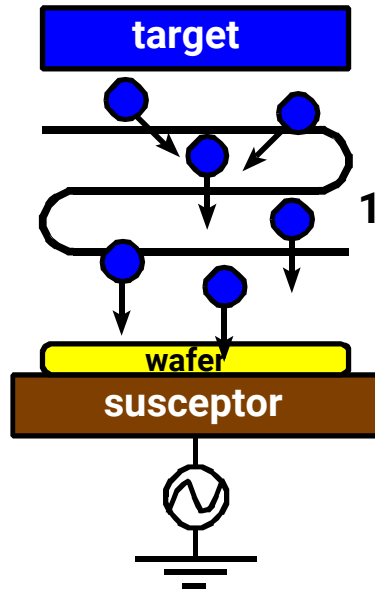
Q12 Please draw a cross-section of a DC magnetron sputtering chamber and name the different parts!



Q13 Which advanced sputtering techniques are possible to improve sidewall coverage in via/trench features?

- 1) Collimated sputtering
- 2) long throw sputtering
- 3) ionized metal deposition

Thin Film Deposition: Sputtering – advanced techniques

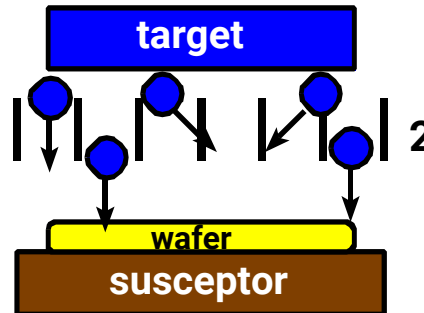


1 water-cooled RF-electrode 1,985 MHz

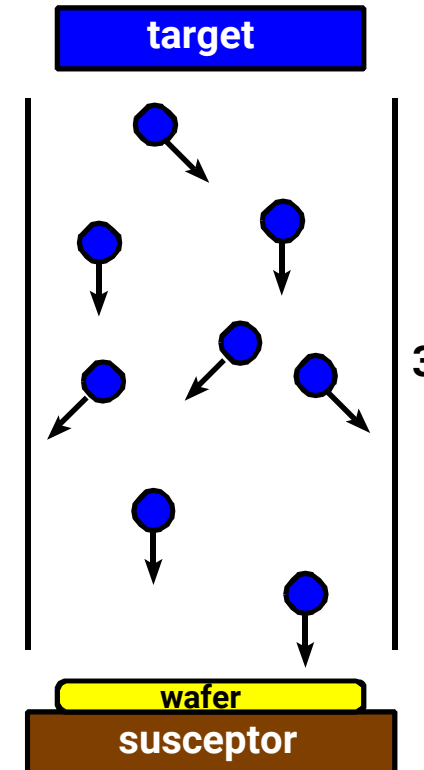
2 collimator

3 chamber wall

ionized metal deposition



collimated sputtering

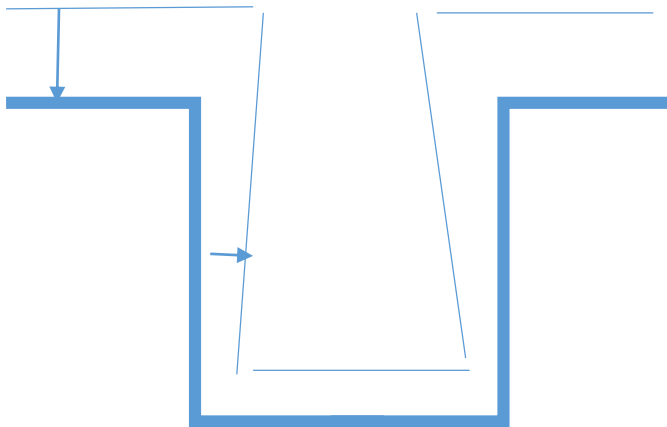


long throw sputtering

Modern principles to coat contact and via holes with a high aspect ratio
(e.g. TiN, TaN or WN barriers for the copper metallization)

Only target particles with a small angle to the substrate normal reach the surface !

Step Coverage:



Step coverage = film thickness in
the feature / film thickness on top

If step coverage is 100%, we have
a conformal film (deposition)